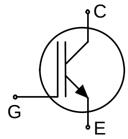
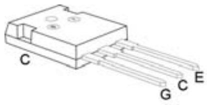
Fast IGBT in NPT-technology



- 40% lower E_{off} compared to previous generation
- Short circuit withstand time – 10 µs
- Designed for:
  - Motor controls
  - Inverter
  - SMPS
- NPT-Technology offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
  - parallel switching capability

PG-TO-220-3-1



PG-TO-247-3

- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/

Type	V_{CE}	I_C	E_{off}	T_j	Marking	Package
SGP15N120	1200V	15A	1.5mJ	150°C	GP15N120	PG-TO-220-3-1
SGW15N120	1200V	15A	1.5mJ	150°C	SGW15N120	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current	I_C		A
T_C = 25°C		30	
T_C = 100°C		15	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	52	
Turn off safe operating area $V_{CE} \le$ 1200V, $T_j \le$ 150°C	-	52	
Gate-emitter voltage	V_{GE}	±20	V
Avalanche energy, single pulse I_C = 15A, V_{CC} = 50V, R_{GE} = 25Ω, start at T_j = 25°C	E_{AS}	85	mJ
Short circuit withstand time[2] V_{GE} = 15V, 100V≤ V_{CC} ≤1200V, $T_j \le$ 150°C	t_{SC}	10	µs
Power dissipation T_C = 25°C	P_{tot}	198	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

[1] J-STD-020 and JESD-022
[2] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.63	K/W
Thermal resistance, junction – ambient	R_{thJA}	PG-TO-220-3-1 PG-TO-247-3	62 40	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=1000µA	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=15A T_j=25°C T_j=150°C	 2.5 -	 3.1 3.7	 3.6 4.3	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=600µA, V_{CE}=V_{GE}	3	4	5	
Zero gate voltage collector current	I_{CES}	V_{CE}=1200V, V_{GE}=0V T_j=25°C T_j=150°C	 - -	 - -	 200 800	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=15A		11	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	V_{CE}=25V,	-	1250	1500	pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	100	120	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	65	80	
Gate charge	Q_{Gate}	V_{CC}=960V, I_C=15A V_{GE}=15V	-	130	175	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	PG-TO-220-3-1 PG-TO-247-3	-	7 13	-	nH
Short circuit collector current[2)]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤5µs 100V≤V_{CC}≤1200V, T_j ≤ 150°C	-	145	-	A

[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=800V, I_C=15A, V_{GE}=15V/0V, R_G=33Ω, L_σ[1])=180nH, C_σ[1])=40pF Energy losses include "tail" and diode reverse recovery.	-	18	24	ns
Rise time	t_r		-	23	30	
Turn-off delay time	$t_{d(off)}$		-	580	750	
Fall time	t_f		-	22	29	
Turn-on energy	E_{on}		-	1.1	1.5	mJ
Turn-off energy	E_{off}		-	0.8	1.1	
Total switching energy	E_{ts}		-	1.9	2.6	

Switching Characteristic, Inductive Load, at T_j=150 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=150°C V_{CC}=800V, I_C=15A, V_{GE}=15V/0V, R_G=33Ω, L_σ[1])=180nH, C_σ[1])=40pF Energy losses include "tail" and diode reverse recovery.	-	38	46	ns
Rise time	t_r		-	30	36	
Turn-off delay time	$t_{d(off)}$		-	652	780	
Fall time	t_f		-	31	37	
Turn-on energy	E_{on}		-	1.9	2.3	mJ
Turn-off energy	E_{off}		-	1.5	2.0	
Total switching energy	E_{ts}		-	3.4	4.3	

[1]) Leakage inductance L_σ and stray capacity C_σ due to dynamic test circuit in figure E.

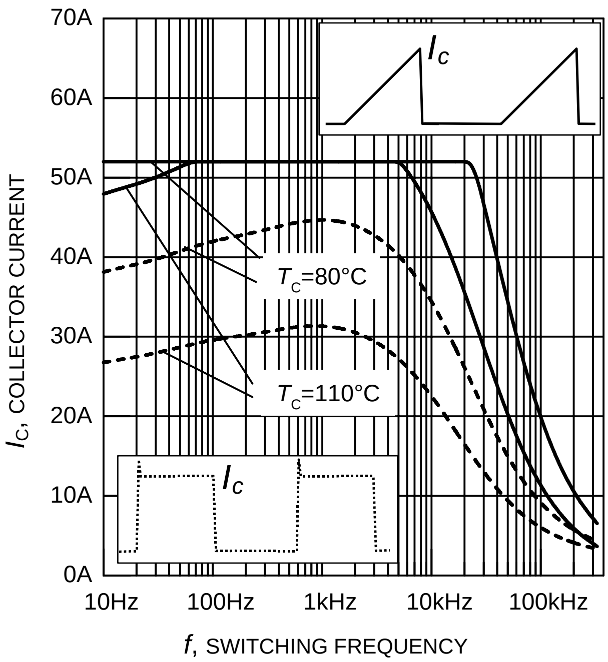


Figure 1. Collector current as a function of switching frequency
($T_j \leq 150°C$, $D = 0.5$, $V_{CE} = 800V$, $V_{GE} = +15V/0V$, $R_G = 33\Omega$)

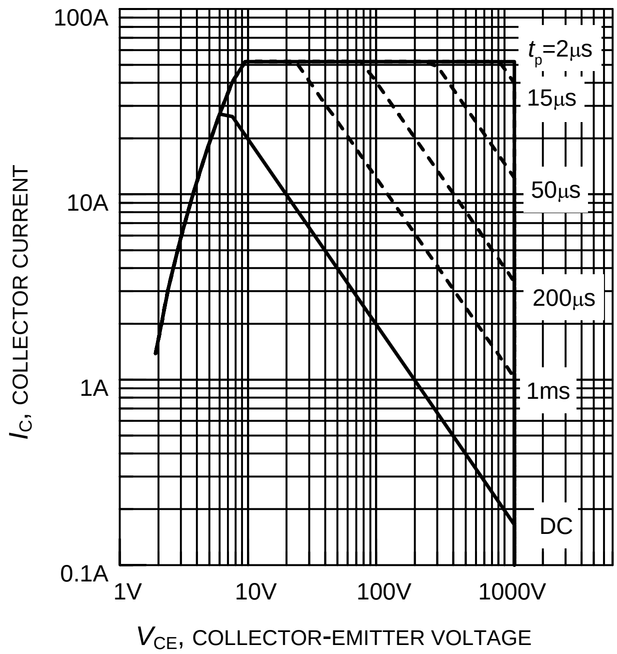


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 150°C$)

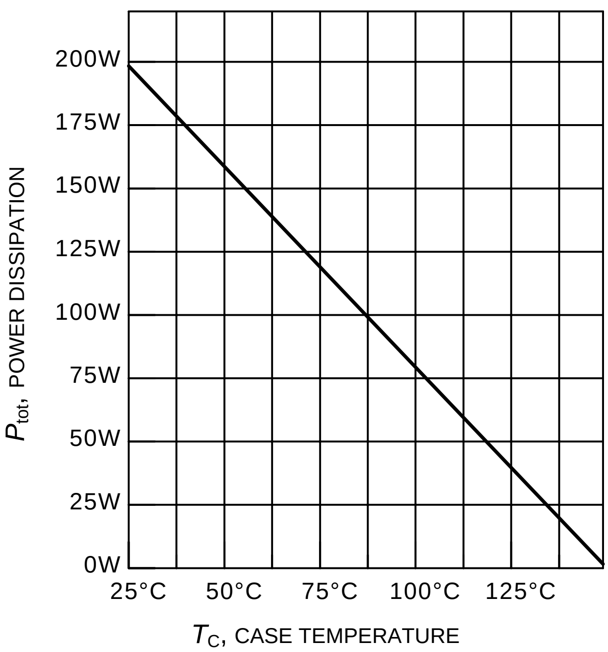


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 150°C$)

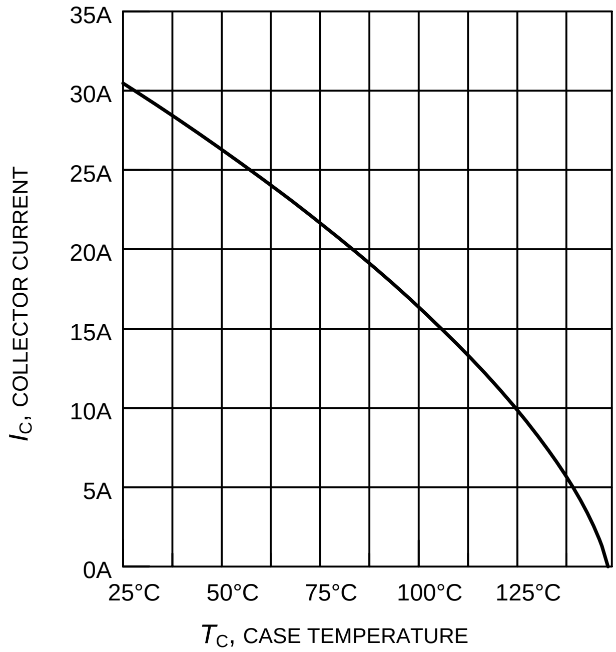


Figure 4. Collector current as a function of case temperature
($V_{GE} \leq 15V$, $T_j \leq 150°C$)

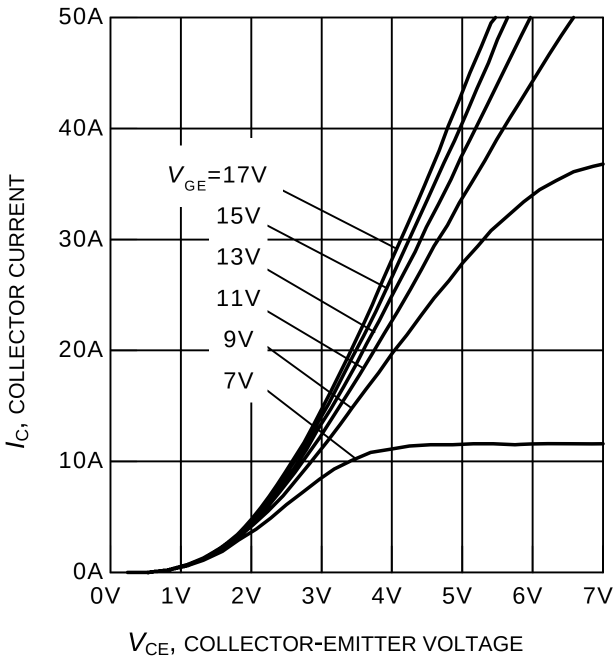


Figure 5. Typical output characteristics
(T_j = 25°C)

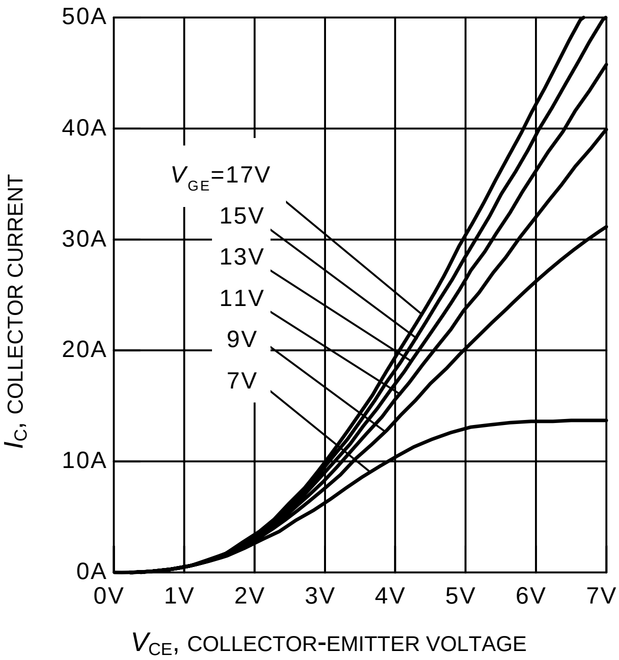


Figure 6. Typical output characteristics
(T_j = 150°C)

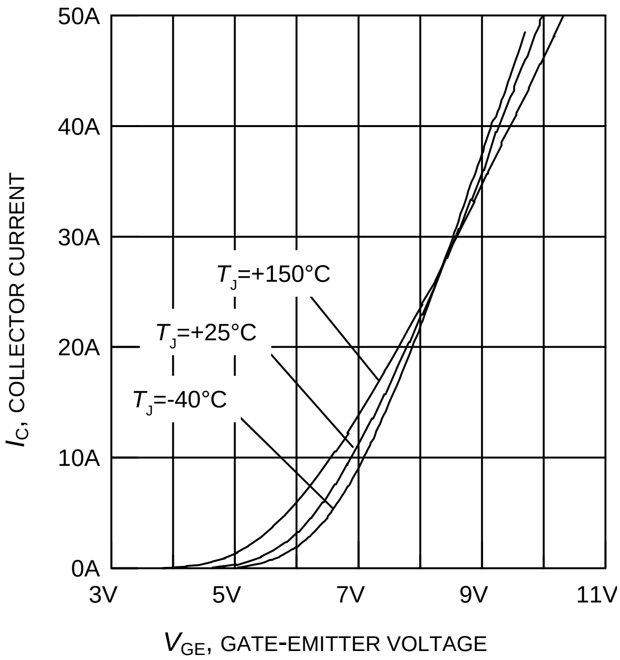


Figure 7. Typical transfer characteristics
(V_{CE} = 20V)

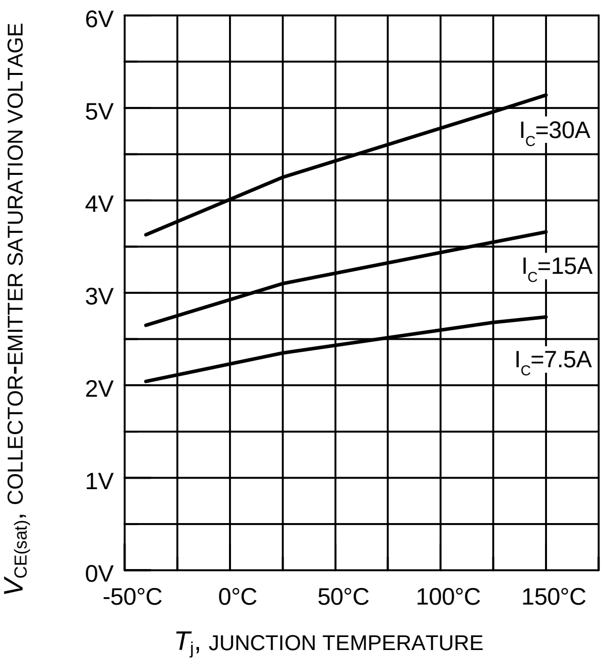


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

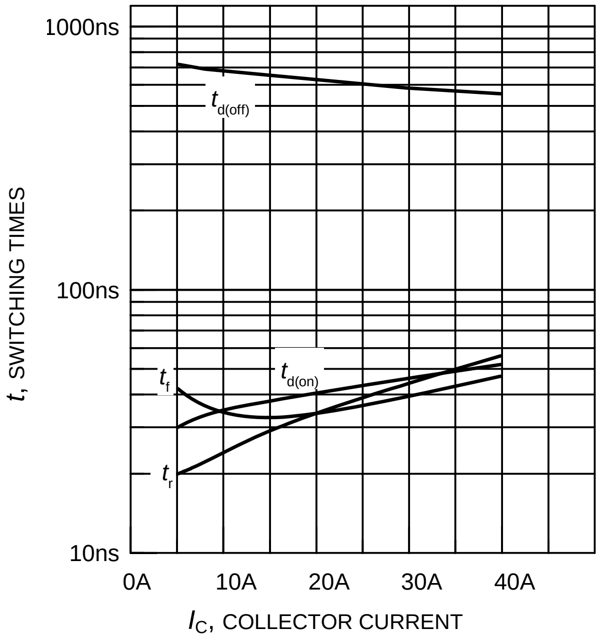


Figure 9. Typical switching times as a function of collector current
(inductive load, T_j = 150°C, V_{CE} = 800V, V_{GE} = +15V/0V, R_G = 33Ω, dynamic test circuit in Fig.E)

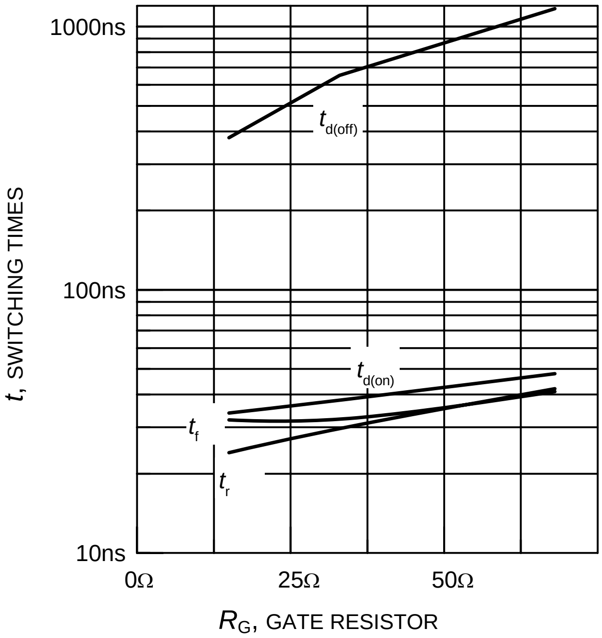


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_j = 150°C, V_{CE} = 800V, V_{GE} = +15V/0V, I_C = 15A, dynamic test circuit in Fig.E)

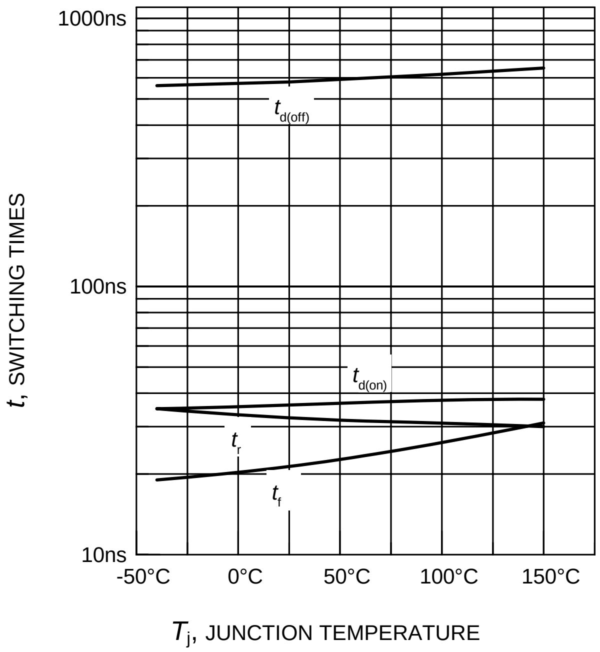


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE} = 800V, V_{GE} = +15V/0V, I_C = 15A, R_G = 33Ω, dynamic test circuit in Fig.E)

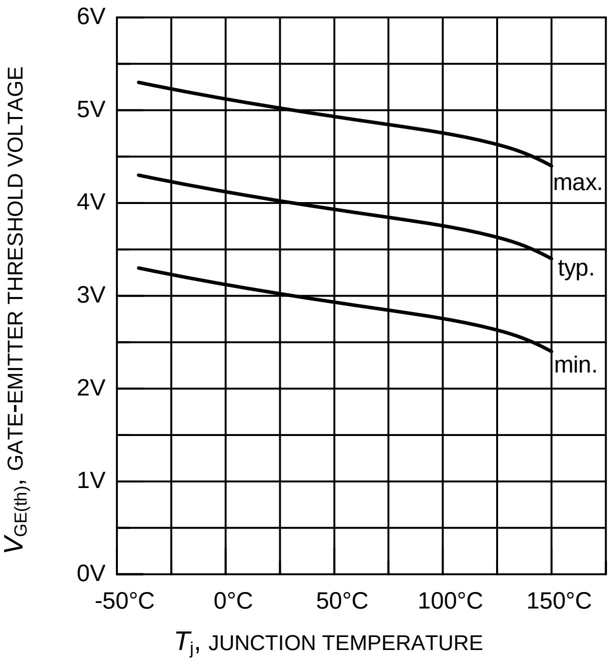


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 0.3mA)

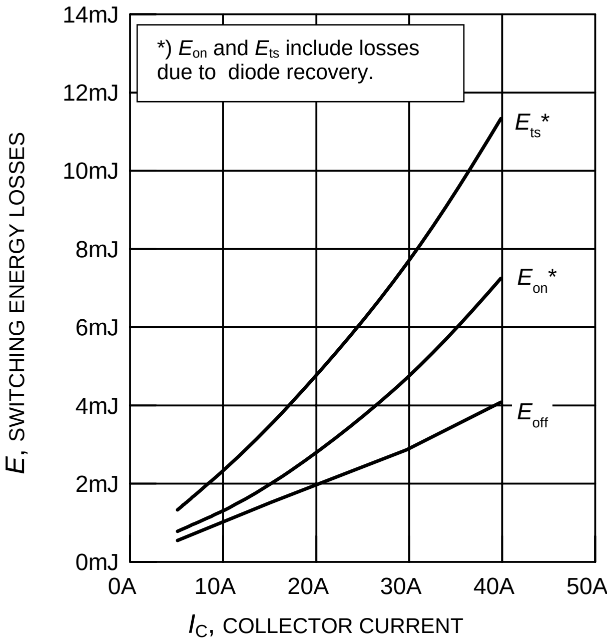


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_j = 150°C,
V_{CE} = 800V, V_{GE} = +15V/0V, R_G = 33Ω,
dynamic test circuit in Fig.E)

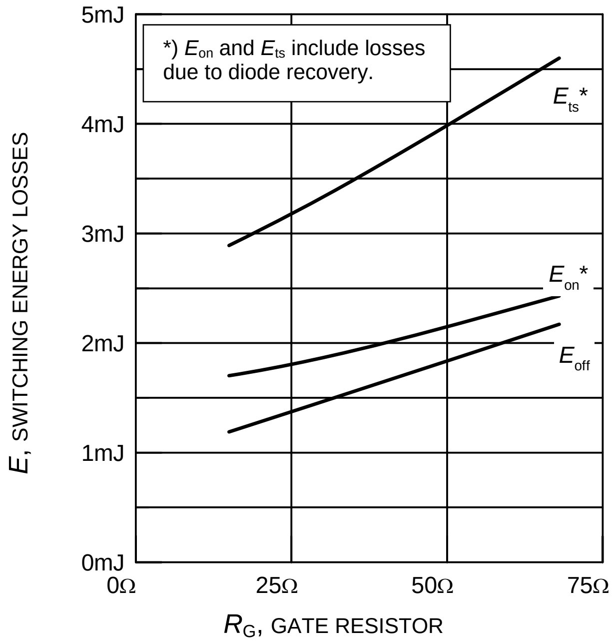


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_j = 150°C,
V_{CE} = 800V, V_{GE} = +15V/0V, I_C = 15A,
dynamic test circuit in Fig.E)

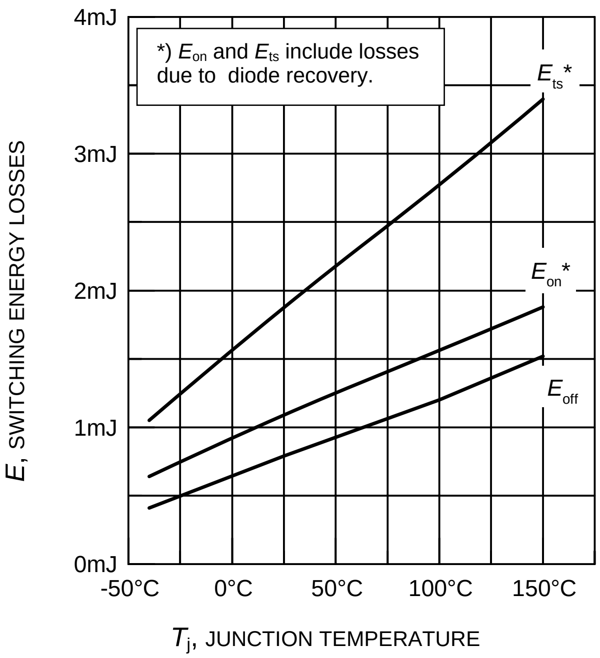


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE} = 800V,
V_{GE} = +15V/0V, I_C = 15A, R_G = 33Ω,
dynamic test circuit in Fig.E)

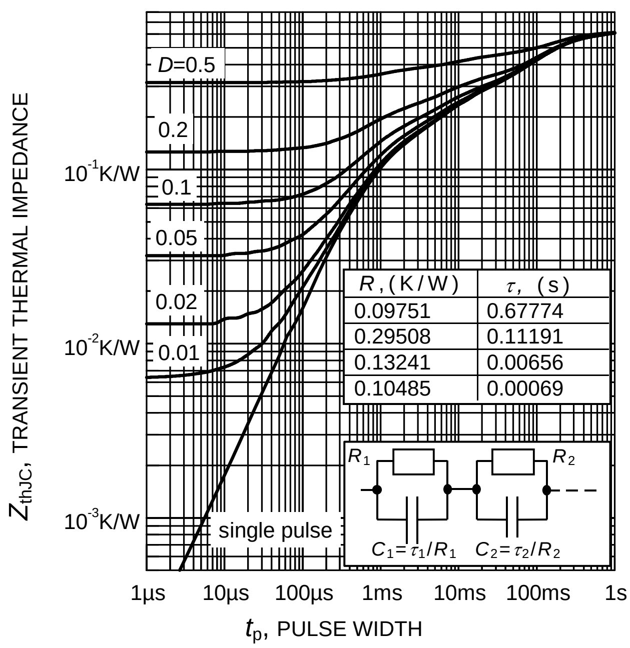


Figure 16. IGBT transient thermal impedance as a function of pulse width
($D = t_p / T$)

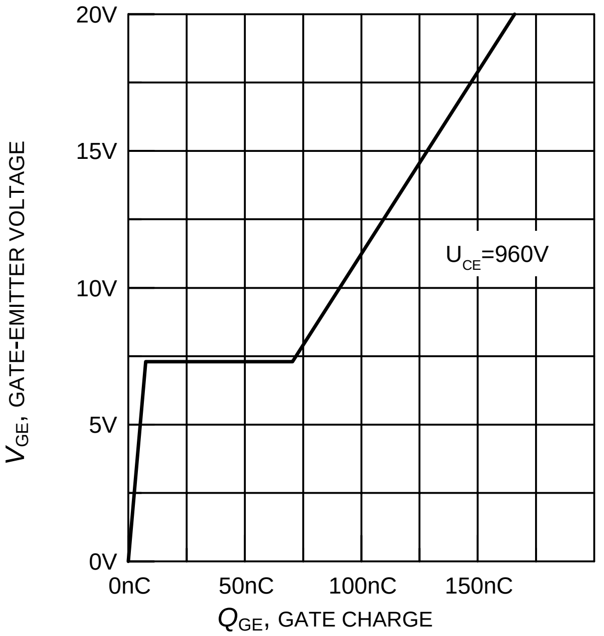


Figure 17. Typical gate charge
(I_C = 15A)

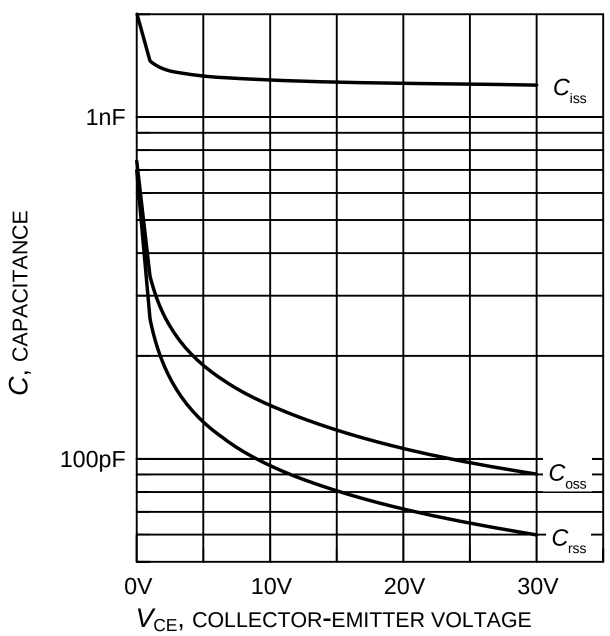


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE} = 0V, f = 1MHz)

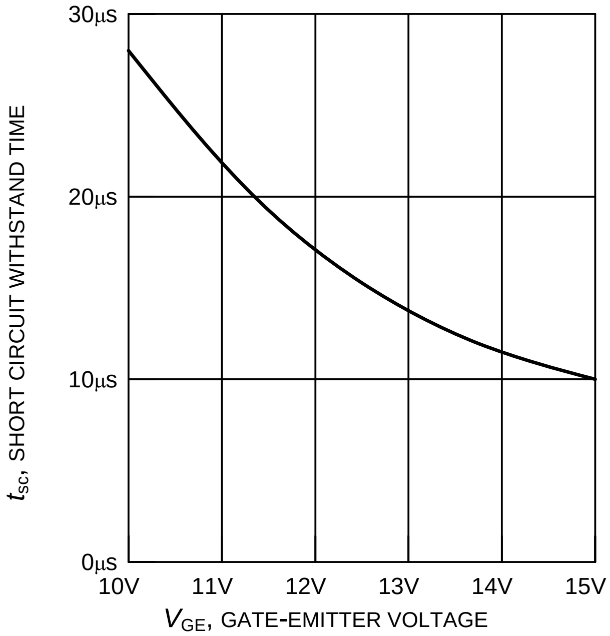


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE} = 1200V, start at T_j = 25°C)

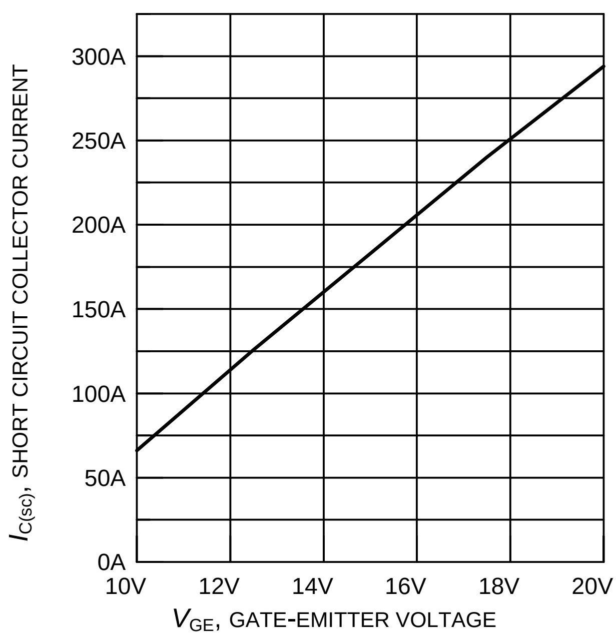


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
(100V≤V_{CE} ≤1200V, T_C = 25°C, T_j ≤ 150°C)

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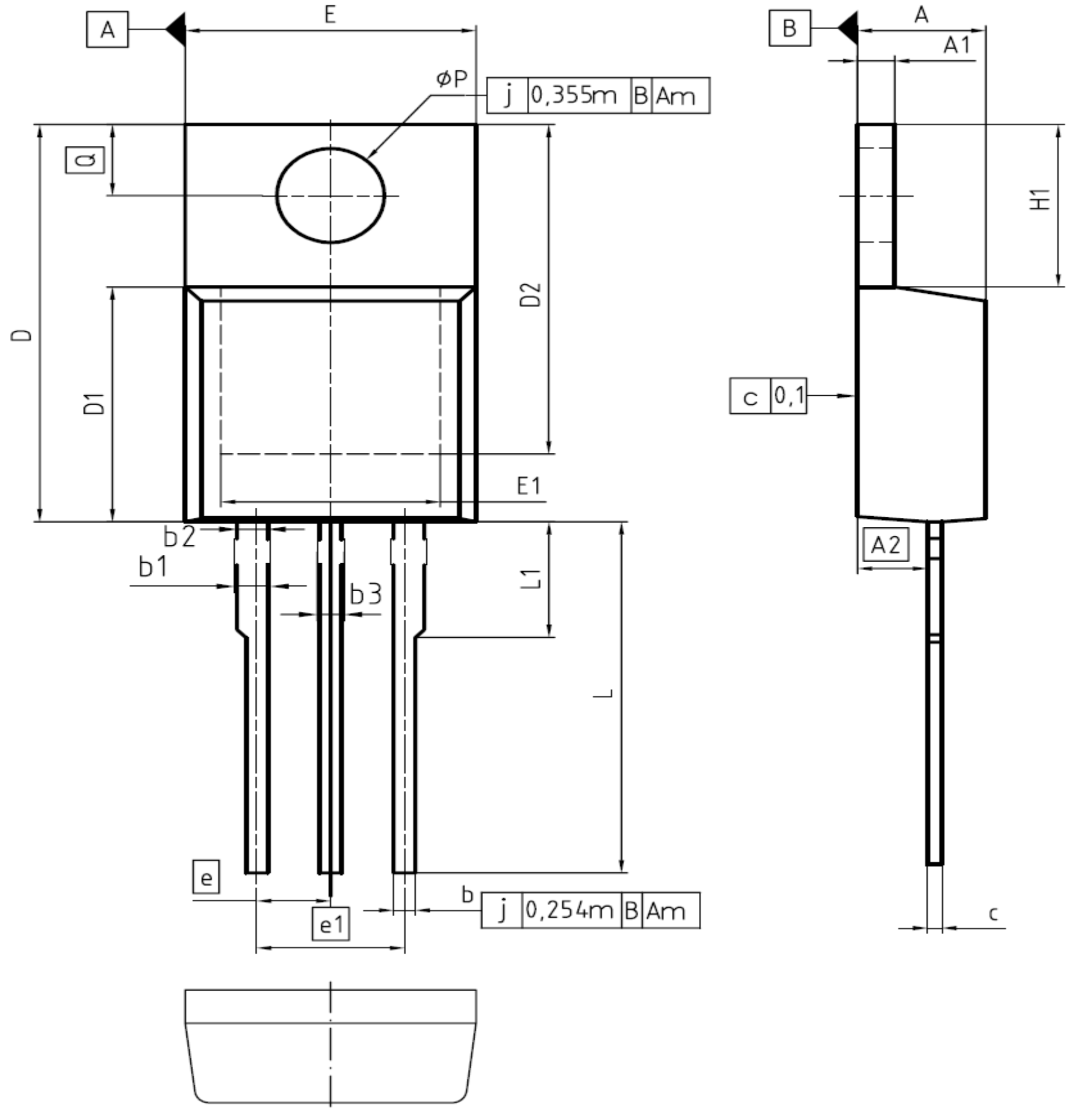

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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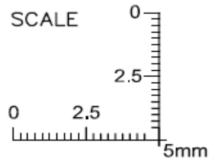
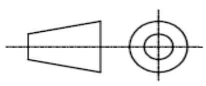


EUROPEAN PROJECTION



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05

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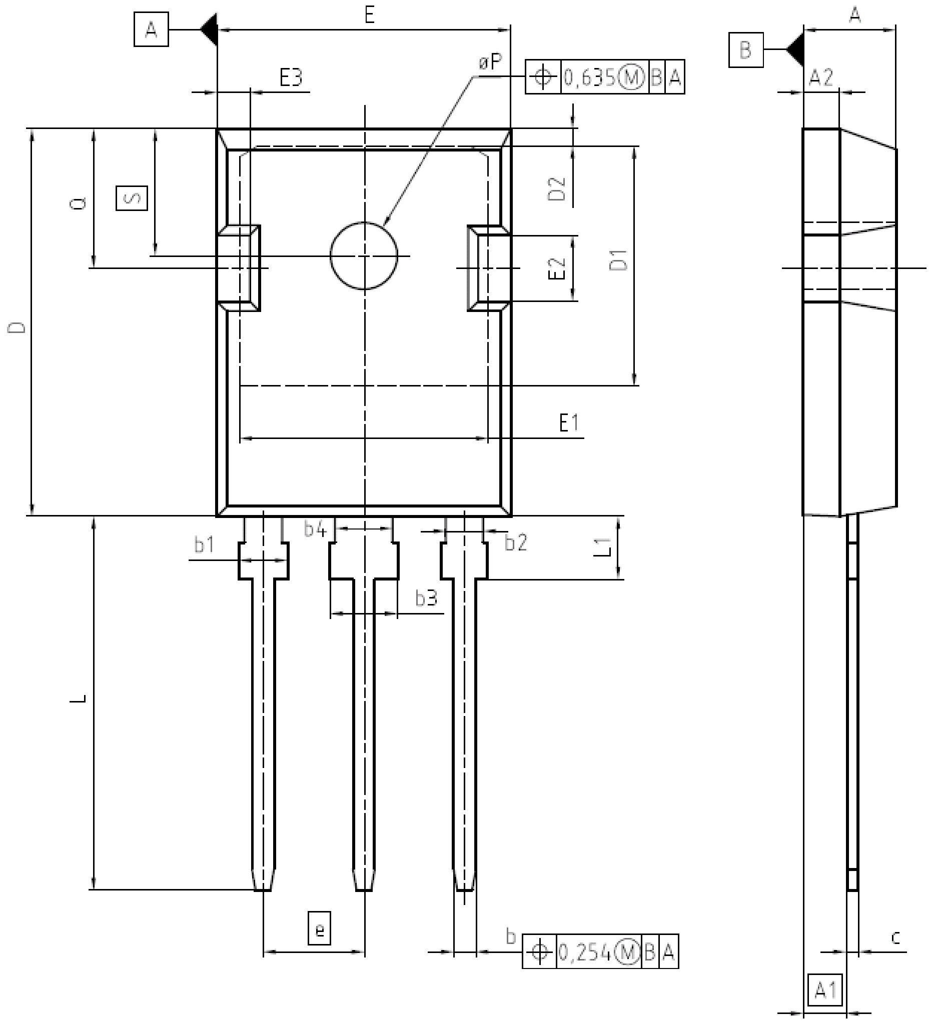

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.16	0.193	0.203
A1	2.27	2.53	0.089	0.099
A2	1.85	2.11	0.073	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.82	21.10	0.820	0.831
D1	16.25	17.65	0.640	0.695
D2	1.05	1.35	0.041	0.053
E	15.70	16.03	0.618	0.631
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.68	2.60	0.066	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.31	0.780	0.799
L1	4.17	4.47	0.164	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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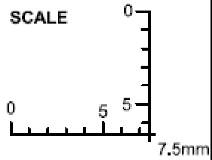
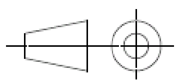


EUROPEAN PROJECTION



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17-12-2007

REVISION
03

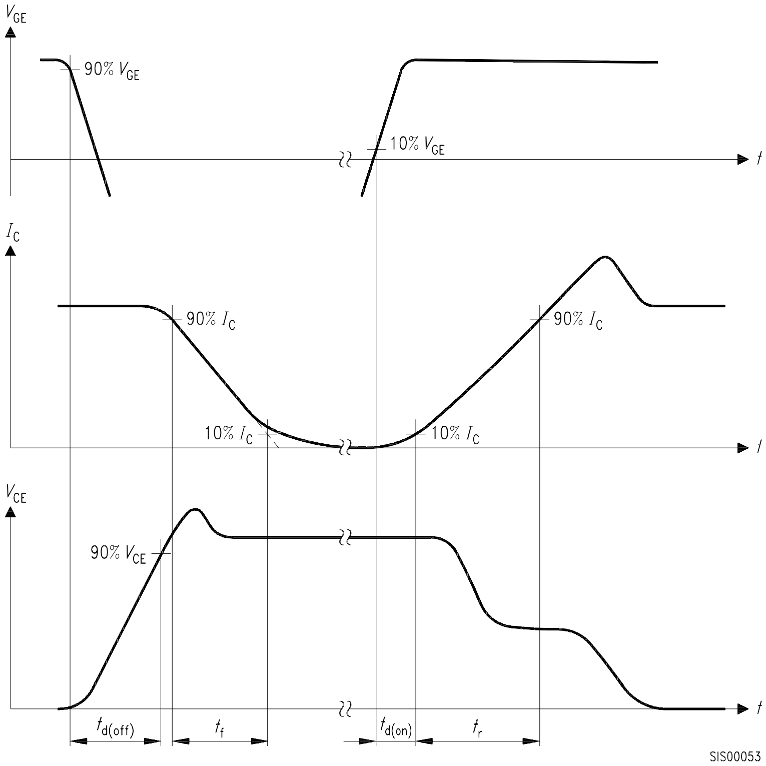

Figure A. Definition of switching times

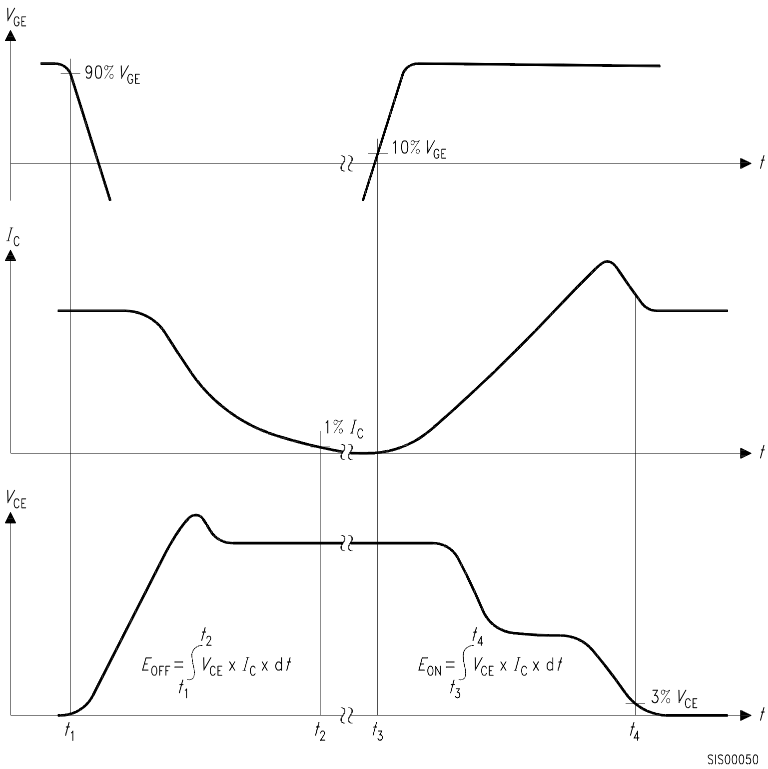

Figure B. Definition of switching losses

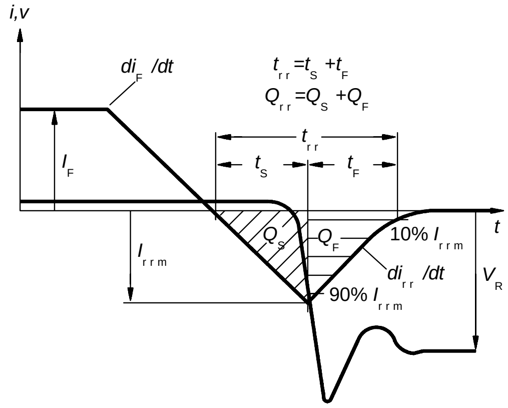

Figure C. Definition of diodes switching characteristics

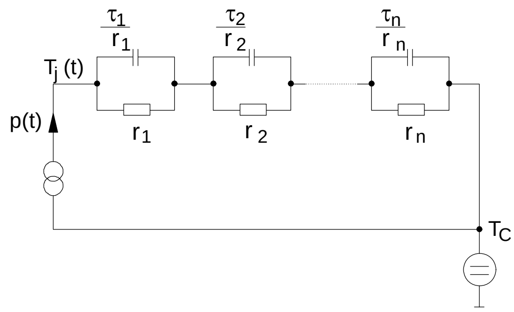

Figure D. Thermal equivalent circuit

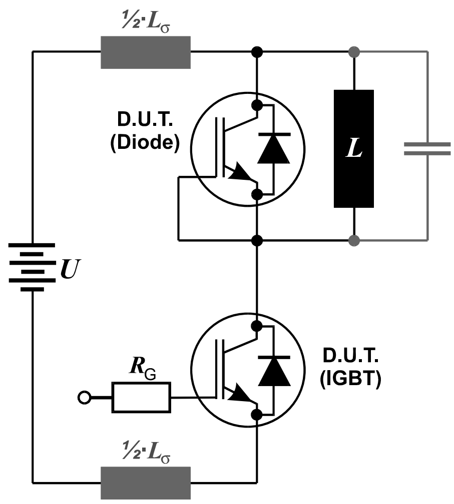

Figure E. Dynamic test circuit
Leakage inductance L_σ=180nH,
and stray capacity C_σ =40pF.

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.